



60V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	Rds(on)	I _D TA = +25°C
601/	390mΩ @ V _{GS} = -10V	-2.3A
-60V	595mΩ @ V _{GS} = -4.5V	-1.9A

Description and Applications

This MOSFET is designed to minimize the on-state resistance yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor control
- DC-DC converters
- Power management functions
- Uninterrupted power supplies

Features and Benefits

- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part.
 A listing can be found at

https://www.diodes.com/products/automotive/automotive-products/.

 This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability.

https://www.diodes.com/quality/product-definitions/

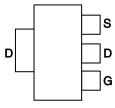
Mechanical Data

- Package: SOT223
- Package Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 ³
- Weight: 0.112 grams (Approximate)

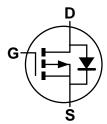
SOT223 (Type DN)



Top View



Pin Out - Top View



Equivalent Circuit

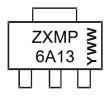
Ordering Information (Note 4)

Part Number	Package	Packing		
Fait Nullibel	Fackage	Qty.	Carrier	
ZXMP6A13GTA	SOT223 (Type DN)	1,000	Tape & Reel	

Notes

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- $4. For packaging details, go to our website at \ https://www.diodes.com/design/support/packaging/diodes-packaging/.$

Marking Information



ZXMP 6A13 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 2 = 2022) WW or \overline{W} W = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		VDSS	-60	V	
Gate-Source Voltage			V_{GS}	±20	V
		(Note 6)		-2.3	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 6)}$	I_{D}	-1.9	Α
		(Note 5)		-1.7	
Pulsed Drain Current	Vgs = 10V	(Note 7)	I _{DM}	-7.8	Α
Continuous Source Current (Body Diode)		(Note 6)	Is	-2.3	Α
Pulsed Source Current (Body Diode) (Note		(Note 7)	Ism	-7.8	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power Dissipation	(Note 5)		2.0 16	W mW/°C	
Linear Derating Factor	(Note 6)	PD	3.9 31		
The second Decistance I longition to Australia	(Note 5)		62.5	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	−−− R _{θJA}	32.0		
Thermal Resistance, Junction to Lead	(Note 8)	Rejl	9.8		
Operating and Storage Temperature Range		TJ, TSTG	-55 to 150	°C	

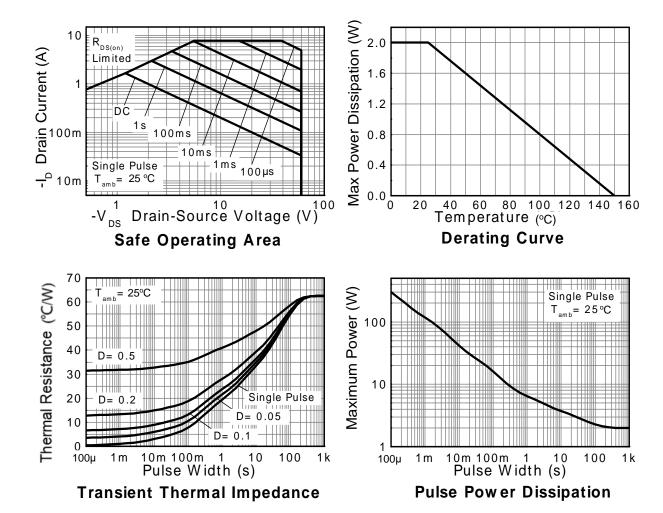
Notes:

- For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 Same as Note 5, except the device is measured at t ≤ 10 sec.
 Same as Note 5, except the device is pulsed with D = 0.02 and pulse width 300µs. The pulse current is limited by the maximum junction temperature.

- 8. Thermal resistance from junction to solder-point (at the end of the drain lead).



Thermal Characteristics





Electrical Characteristics (@T_A = +25°C unless otherwise specified.)

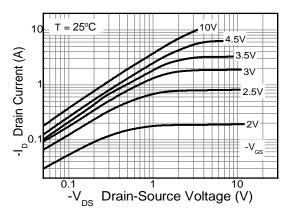
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BVDSS	-60		_	V	$I_D = -250\mu A$, $V_{GS} = 0V$	
Zero Gate Voltage Drain Current	IDSS	_		-0.5	μΑ	$V_{DS} = -60V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	Vgs(TH)	-1.0	_	-3.0	V	$I_D = -250\mu A$, $V_{DS} = V_{GS}$	
Statio Drain Source On Registance (Note 0)	Dagger			0.390	Ω	$V_{GS} = -10V, I_{D} = -0.9A$	
Static Drain-Source On-Resistance (Note 9)	RDS(ON)	_	_	0.595	12	$V_{GS} = -4.5V$, $I_{D} = -0.8A$	
Forward Transconductance (Notes 9 & 10)	g fs	_	1.8	_	S	$V_{DS} = -15V, I_{D} = -0.9A$	
Diode Forward Voltage (Note 9)	VsD	_	-0.85	-0.95	V	$I_S = -0.8A$, $V_{GS} = 0V$, $T_J = +25$ °C	
Reverse Recovery Time (Note 10)	t _{RR}		21.1	_	ns	$I_S = -0.9A$, di/dt = 100A/ μ s,	
Reverse Recovery Charge (Note 10)	Q _{RR}	_	19.3	_	nC	$T_J = +25$ °C	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss	_	219	_	pF	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
Output Capacitance	Coss	_	25.7		pF	$V_{DS} = -30V, V_{GS} = 0V$ - f = 1MHz	
Reverse Transfer Capacitance	Crss	_	20.5	_	pF	71 = 11VII 12	
Total Gate Charge (Note 11)	Qg	_	2.9	_	nC	V _{GS} = -4.5V	
Total Gate Charge (Note 11)	Qg	_	5.9	_	nC	V _{DS} = -30V	
Gate-Source Charge (Note 11)	Qgs	_	0.74	_	nC	$V_{GS} = -10V$ $I_{D} = -0.9A$	
Gate-Drain Charge (Note 11)	Qgd	_	1.5	_	nC	1	
Turn-On Delay Time (Note 11)	tD(ON)	_	1.6	_	ns		
Turn-On Rise Time (Note 11)	t _R	_	2.2	_	ns	V_{DD} = -30V, V_{GS} = -10V I_D = -1A, $R_G \cong 6.0\Omega$	
Turn-Off Delay Time (Note 11)	tD(OFF)	_	11.2	_	ns		
Turn-Off Fall Time (Note 11)	t _F	_	5.7	_	ns]	

Notes:

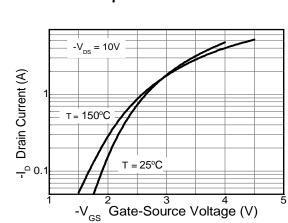
^{9.} Measured under pulsed conditions. Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$ 10. For design aid only, not subject to production testing. 11. Switching characteristics are independent of operating junction temperatures.



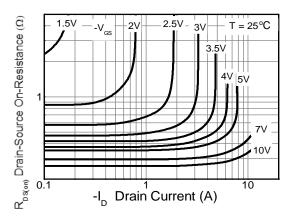
Typical Characteristics



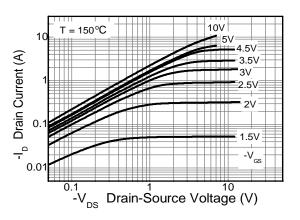
Output Characteristics



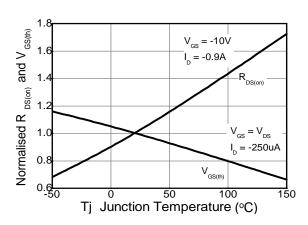
Typical Transfer Characteristics



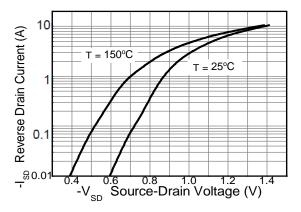
On-Resistance v Drain Current



Output Characteristics



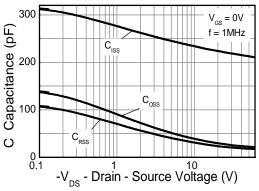
Normalised Curves v Temperature



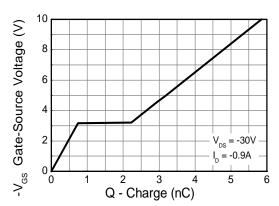
Source-Drain Diode Forward Voltage



Typical Characteristics (continued)

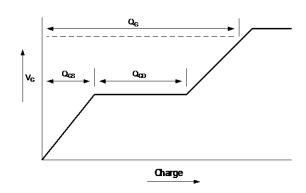


Capacitance v Drain-Source Voltage

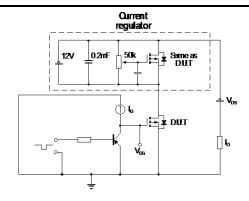


Gate-Source Voltage v Gate Charge

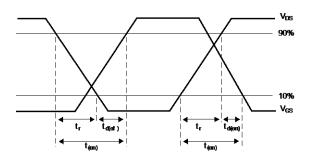
Test Circuits



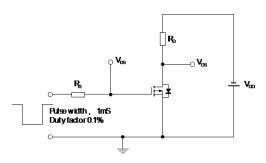
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



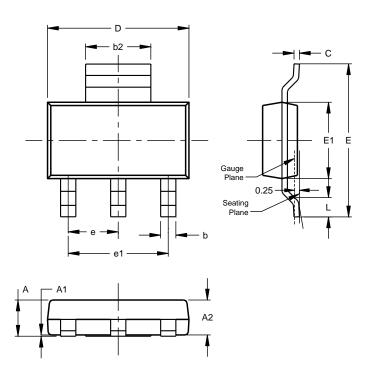
Switching time test circuit



Package Outline Dimensions

 $\label{please} Please see \ http://www.diodes.com/package-outlines.html \ for the latest version.$

SOT223 (Type DN)

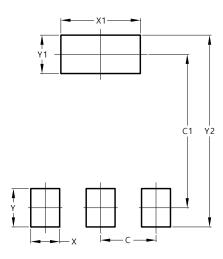


SOT223 (Type DN)				
Dim	Min	Max	Тур	
Α		1.70		
A1	0.01	0.15	-	
A2	1.50	1.68	1.60	
b	0.60	0.80	0.70	
b2	2.90	3.10		
С	0.20	0.32		
D	6.30	6.70		
Е	6.70	7.30		
E1	3.30	3.70		
е			2.30	
e1			4.60	
L	0.85			
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
C	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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